

/ Descriptions

TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

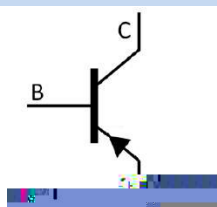
2SC3422

Good linearity of h_{FE} , complementary to 2SC3422.

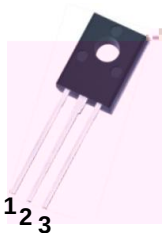
/ Applications

Audio frequency power amplifier and low speed switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	O	Y	GR
h_{FE} Range	80 160	120 240	200 400

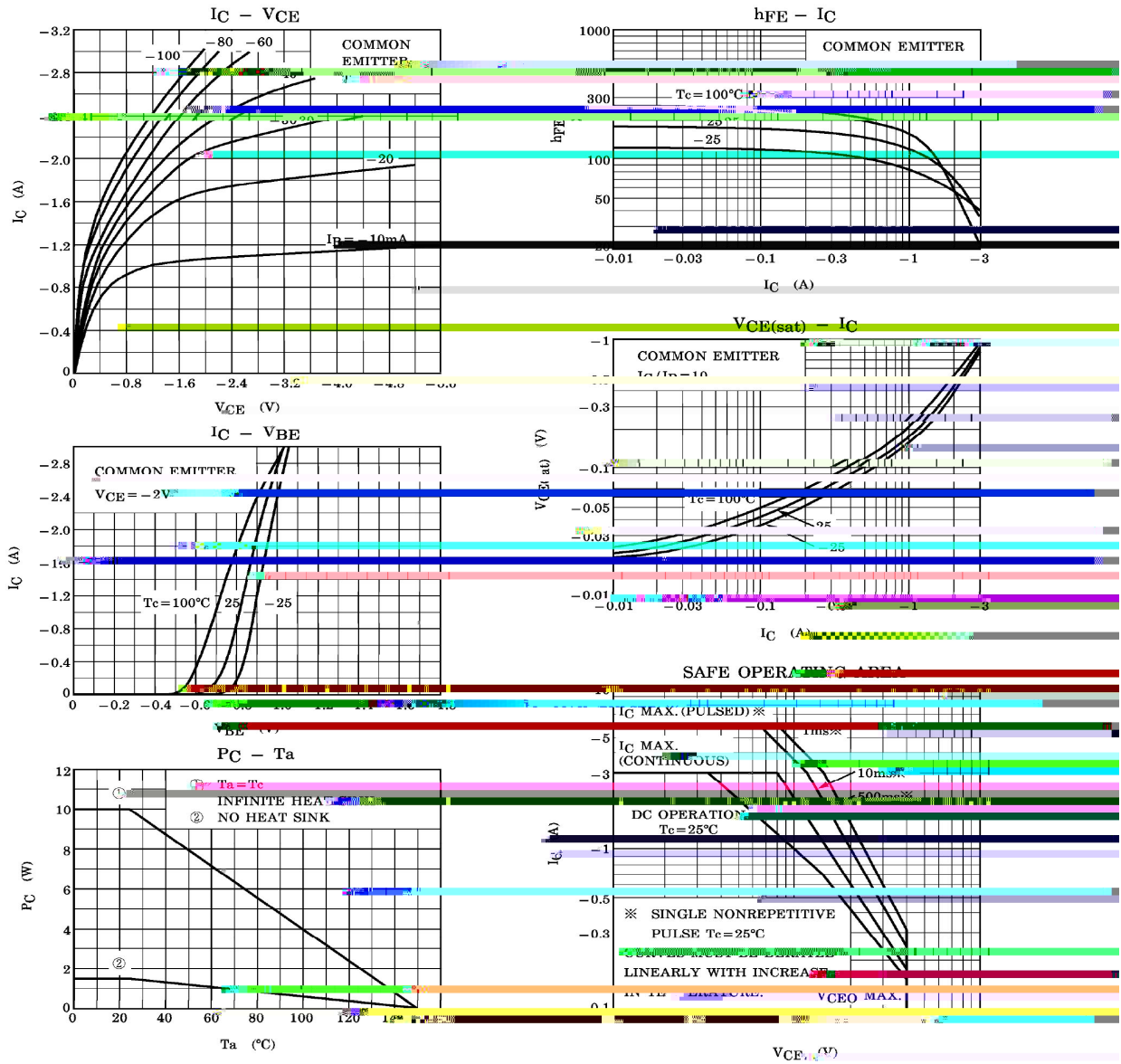
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Base Current – Continuous	I_B	-1.0	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	$P (T = 25)$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

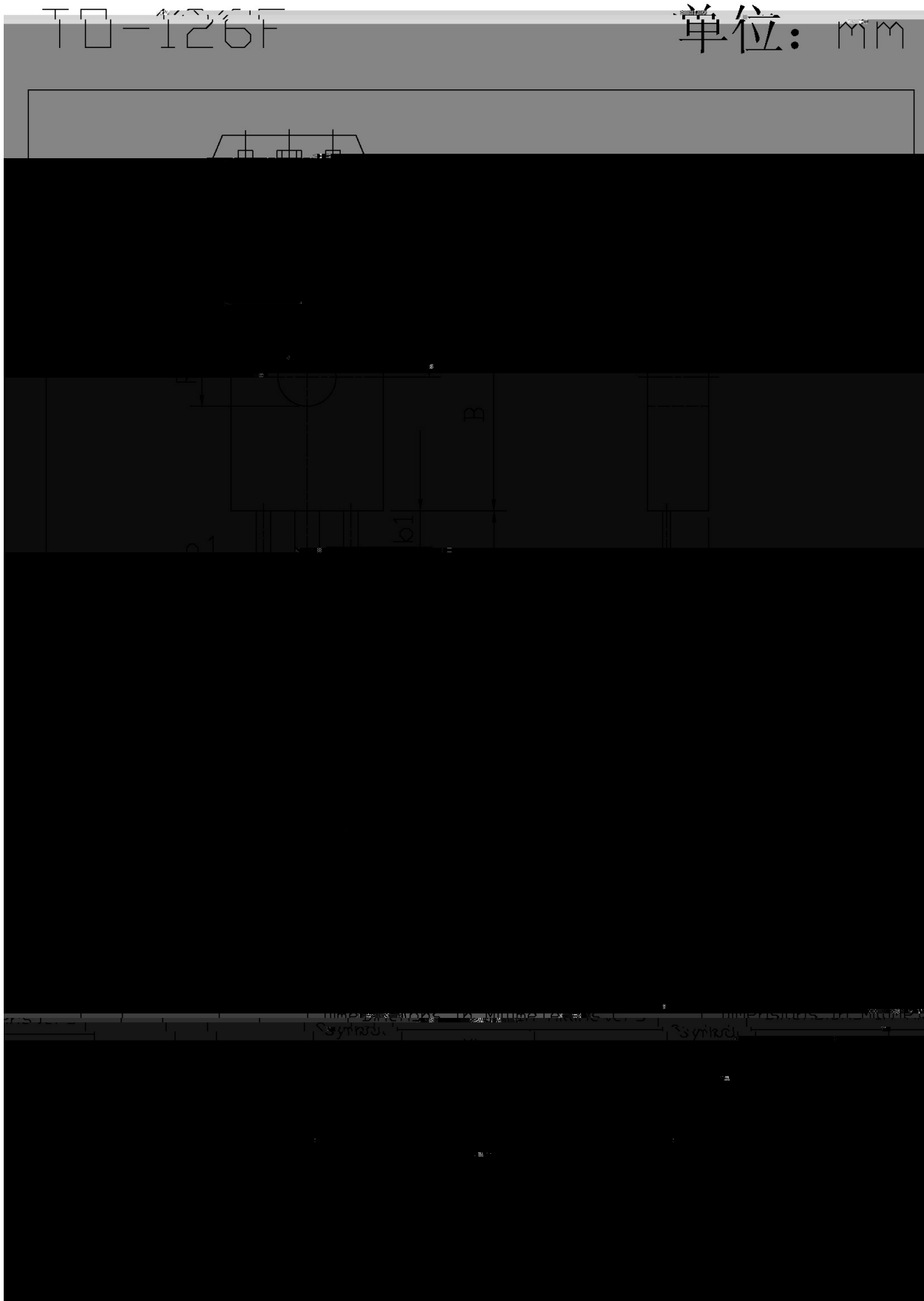
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB} \quad E=0$				μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} \quad C=0$		-0.1		μA
Collector to Emitter Breakdown	V_{CEO}	$I_C = -10mA \quad I_B = 0$	-40			
DC Current Gain	$h_{FE(1)}$	$V_{CE} \quad C = -0.5A$	80	400		
	$h_{FE(2)}$	$V_{CE} \quad C = -2.5A$	25			
Voltage	$V_{CE(sat)}$	$I_C = -2.0A \quad I_B = -0.2A$		-0.8		V
Base to Emitter Voltage	V_{BE}	$V_{CE} \quad C = -0.5A$		-1.0		V
Transition Frequency	f_T	$V_{CE} \quad C = -0.5A$		100		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} \quad E=0$ $f=1.0MHz$		35		pF

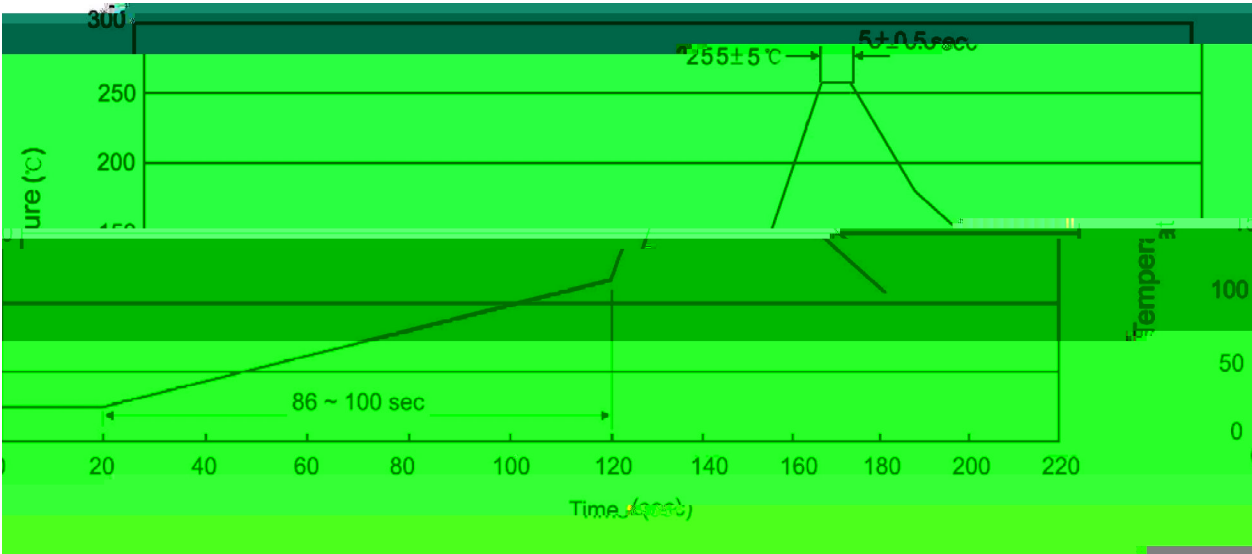
/ Electrical Characteristic Curve



/ Package Dimensions



() / Temperature Profile for Dip Soldering(Pb-Free)



- Note:
- 1.Preheating:25~150 , Time:60~90sec.
 - 2.Peak Temp.:255±5 , Duration:5±0.5sec.
 - 3. Cooling Speed: 2~10 /sec.

- 1 25 150 60 90sec;
- 2 255±5 5±0.5sec;
- 3 2 10 /sec.

255±